Yu M Khoverko

List of Publications by Year
in descending order

84	425	567144 15	794469 19
papers	citations	h-index	g-index

86	86	86	72
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Strain-induced effects in p-type Si whiskers at low temperatures. Materials Science in Semiconductor Processing, 2015, 40, 766-771.	1.9	27
2	Strain effect on magnetoresistance of SiGe solid solution whiskers at low temperatures. Materials Science in Semiconductor Processing, 2011, 14, 18-22.	1.9	24
3	Low temperature magnetoresistance of InSb whiskers. Materials Science in Semiconductor Processing, 2015, 40, 550-555.	1.9	21
4	Variableâ€range hopping conductance in Si whiskers. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 504-508.	0.8	20
5	Magneto-transport properties of poly-silicon in SOI structures at low temperatures. Materials Science in Semiconductor Processing, 2015, 31, 19-26.	1.9	20
6	Properties of Low-Dimentional Polysilicon in SOI Structures for Low Temperature Sensors. Advanced Materials Research, 2013, 854, 49-55.	0.3	19
7	Magnetic susceptibility and magnetoresistance of neutron-irradiated doped SI whiskers. Journal of Magnetism and Magnetic Materials, 2015, 393, 310-315.	1.0	19
8	Negative magnetoresistance in indium antimonide whiskers doped with tin. Low Temperature Physics, 2016, 42, 453-457.	0.2	19
9	Magnetic Properties of Doped Si<B,Ni> Whiskers for Spintronics. Journal of Nano Research, 2016, 39, 43-54.	0.8	18
10	Properties of Doped GaSb Whiskers at Low Temperatures. Nanoscale Research Letters, 2017, 12, 156.	3.1	18
11	High Sensitive Active MOS Photo Detector on the Local 3D SOI-Structure. Advanced Materials Research, 2013, 854, 45-47.	0.3	17
12	Impedance spectroscopy of polysilicon in SOI structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 156-159.	0.8	17
13	Peculiarities of magnetoresistance in InSb whiskers at cryogenic temperatures. Materials Research Bulletin, 2015, 72, 324-330.	2.7	17
14	Low-temperature magnetoresistance of GaSb whiskers. Low Temperature Physics, 2017, 43, 692-698.	0.2	17
15	Polysilicon on Insulator Structures for Sensor Application at Electron Irradiation & Magnetic Fields. Advanced Materials Research, 2011, 276, 109-116.	0.3	16
16	Nanoscale Conductive Channels in Silicon Whiskers with Nickel Impurity. Nanoscale Research Letters, 2017, 12, 78.	3.1	16
17	Magnetic Susceptibility of Doped Si Nanowhiskers. Journal of Nanoscience and Nanotechnology, 2012, 12, 8690-8693.	0.9	15
18	Berry phase in strained InSb whiskers. Low Temperature Physics, 2018, 44, 1189-1194.	0.2	12

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19	Spin-related phenomena in nanoscale Si <â€¯B, Ni> whiskers. Journal of Magnetism and Magnetic Materials, 2019, 473, 331-334.	1.0	11
20	Superconductivity and Kondo Effect of PdxBi2Se3 Whiskers at Low Temperatures. Journal of Nano- and Electronic Physics, 2017, 9, 05013-1-05013-5.	0.2	8
21	The Device-Technological Simulation of The Field-Emission Micro-Cathodes Based on Three-Dimensional Soi-Structures. ECS Transactions, 2008, 14, 569-580.	0.3	7
22	Impedance of boron and nickel doped silicon whiskers. Molecular Crystals and Liquid Crystals, 2018, 661, 12-19.	0.4	7
23	Superconductivity and weak localization of PdxBi2Se3 whiskers at low temperatures. Applied Nanoscience (Switzerland), 2018, 8, 877-883.	1.6	6
24	Nanoscale polysilicon in sensors of physical values at cryogenic temperatures. Journal of Materials Science: Materials in Electronics, 2018, 29, 8364-8370.	1.1	6
25	Spin-orbit interaction in InSb core-shell wires. Molecular Crystals and Liquid Crystals, 2018, 674, 1-10.	0.4	4
26	Rashba Interaction in Polysilicon Layers SemOI-Structures. Journal of Electronic Materials, 2019, 48, 4934-4938.	1.0	4
27	Superconductivity and weak anti-localization in GaSb whiskers under strain. Low Temperature Physics, 2019, 45, 1065-1071.	0.2	4
28	Laser-Recrystallized SOI Layers for Sensor Applications at Cryogenic Temperatures. , 2002, , 233-237.		4
29	The spin-resolved electronic structure of doped crystals siâ€‰<â€‰Niâ€‰>â€‰and Siâ€‰<â€‰B, Ni>: theoretical and experimental aspects. Molecular Crystals and Liquid Crystals, 2018, 674, 120-129.	0.4	3
30	Magnetoresistance of GaP0.4As0.6 Whiskers in Vicinity of MIT. Journal of Nano- and Electronic Physics, 2019, 11, 04007-1-04007-5.	0.2	3
31	Quantization in magnetoresistance of strained InSb whiskers. Low Temperature Physics, 2019, 45, 513-517.	0.2	2
32	Strain-Induced Berry Phase in GaSb Microcrystals. Journal of Low Temperature Physics, 2019, 196, 375-385.	0.6	2
33	Spin-orbit coupling in strained Ge whiskers. Low Temperature Physics, 2019, 45, 1182-1186.	0.2	2
34	Effect of the strong electron correlation on the spin-resolved electronic structure of the doped crystals Siâ€‰<â€‰B, Fe>, Siâ€‰<â€‰B, Coâ€‰>â€‰and Siâ€‰<â€‰B, Ni>. Molecular Crystals and Liquid Crysta 700, 1-12.	0.4	2
35	PHYSICAL SENSORS BASED ON SILICON- ON- INSULATOR STRUCTURES WITH RECRYSTALLIZED POLYSILICON LAYER. Sensor Electronics and Microsystem Technologies, 2014, 5, 17-26.	0.1	2
36	Peculiarities of charge carriers transport in submicron Si-Ge whiskers. Functional Materials, 2015, 22, 27-33.	0.4	2

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37	<title>Recrystallized polysilicon on insulating substrates as a material for optoelectronic sensors</title>. , 1999, , .		1
38	Weak Antilocalization Model of N-Type Bi2Se3 Whiskers. , 2018, , .		1
39	SOI p-MOS Biosensor Circuit-Layout Simulation. , 2019, , .		1
40	Temperature Sensors Based on Metal-Silicon Microstructure for Microsystem Technology. , 2019, , .		1
41	Quantum magnetoresistance in Si <B, Ni> whiskers. Low Temperature Physics, 2021, 47, 488-492.	0.2	1
42	Polysilicon-on-Insulator Layers at Cryogenic Temperatures and High Magnetic Fields. , 2005, , 297-302.		1
43	Spin-orbit Splitting of Valence Band in Silicon Whiskers under Strain. Journal of Nano- and Electronic Physics, 2019, 11, 02019-1-02019-8.	0.2	1
44	Carrier transport in laser-recrystallized polysilicon layers for microelectronic devices and sensors. , 0, , .		0
45	The frequency dependence features of Si whiskers conductance in low-temperature range. , 2016, , .		0
46	Electron irradiation effect on resistance of SOI structures. , 2016, , .		0
47	Electrical and layouts simulation of analytical microsystem-on-chip elements for high frequence and low temperature applications. , 2016, , .		0
48	Magnetoresistance oscillations in germanium and indium antimonide whiskers. , 2016, , .		0
49	Polysilicon in SOI-structures as a material for sensor application in the wide temperature range. , 2016, , .		0
50	Components of micro- and nanoelectronics based on silicon structures for cryogenic temperatures. , 2016, , .		0
51	Deformation characteristics of SOI structures at cryogenic temperatures. , 2017, , .		0
52	Peculiarities of magnetoresistance in Si whiskers dopped Ni at cryogenic temperatures. , 2017, , .		0
53	Magnetoresistance oscillations in InSb and GaSb whiskers at low temperatures. , 2017, , .		0
54	Magnetoresistance of doped Te:GaSb whiskers. , 2017, , .		0

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55	Multifunctional sensors based on Si < B, Ni > microcrystals for Harsh environment. , 2018, , .		0
56	Spin-Dependent Transport of Charge Carriers in Silicon Microcrystals Doped with Boron and Diluted with Nickel. , 2018, , .		0
57	Magnetoresistance of GaP₀₄ As₀₆ whiskers at low temperatures. , 2018, , .		0
58	3D MOS-transistor elements in smart-sensors based on SOI-structures. , 2018, , .		0
59	MSoC device based on SOI-structures. , 2018, , .		0
60	Deformation-induced Magnetoconductance in Silicon Whiskers near Metal-insulator Transition. , 2019, , .		0
61	Modelling and Fabrication of the Silicon-Based Device Structures for Microelectronic Applications. , 2019, , .		0
62	Strain-induced Magnetoconductance in Germanium Whiskers. , 2019, , .		0
63	Spin-dependent Transport of DMS on the Base Silicon Whiskers: Impedance, Structure and Properties. , 2019, , .		0
64	Weak Localization in GaSb Whiskers under Strain Influence. , 2019, , .		0
65	Development of Multitextures on the Basis of Porous Silicon for High Performance Photoelectric Converters. , 2019, , .		0
66	Giant Magnetoresistance in the Deformed Microcrystals of Indium Antimonide. , 2020, , .		0
67	Magneto-transport properties of Bi2Se3 whiskers: superconductivity and weak localization. Molecular Crystals and Liquid Crystals, 2020, 701, 82-90.	0.4	0
68	Simulation of Sensor Capacitive Elements Built into the Microsystem-On-Chip. , 2020, , .		0
69	Frequency response in polycrystalline silicon films of SemOI-structures. , 2020, , .		0
70	L-C- Electronic Elements Based on Silicon Microstructures. , 2020, , .		0
71	Strain-induced splitting in valence band of Siâ€“Ge whiskers. Applied Nanoscience (Switzerland), 0, , 1.	1.6	0
72	Simulation An Integrated Sensor As An Element Of CMOS Inverter. , 2021, , .		0

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73	Critical fields and features of electromagnetic transport of Bi2Se3 whiskers at low temperatures. Low Temperature Physics, 2021, 47, 96-100.	0.2	0
74	Magnetoconductance of Polycrystalline Silicon in SemOI-structures for Sensors Application. , 2021, , .		0
75	The spin-resolved electronic structure of the codoped crystals Siâ€‰<â€‰B, V>, Siâ€‰<â€‰B, Crâ€‰>â€‰and Siâ€‰<â€‰B, Mn>. Molecular Crystals and Liquid Crystals, 2021, 721, 62-73.	0.4	0
76	Transport Phenomena for Development Inductive Elements Based on Silicon Wires. Journal of Nano- and Electronic Physics, 2018, 10, 02038-1-02038-5.	0.2	0
77	Features of the Surface Conductivity of Silicon Microstructures at Low Temperatures. MÃ¬krosistemi, ElektronÃ¬ka Ta Akustika, 2018, 23, 6-13.	0.2	0
78	Development of Silicon-Based Structures for Micro-and Nanosystem Devices Operable in Harsh Conditions. , 2018, , .		0
79	Thermoelectric Properties of InSb Whiskers. Journal of Nano- and Electronic Physics, 2020, 12, 05017-1-05017-4.	0.2	0
80	Superparamagnetism in Si1 â€“ xGex (B, Hf) Whiskers. Journal of Nano- and Electronic Physics, 2021, 13, 06019-1-06019-5.	0.2	0
81	Si-Ge whiskers for thermoelectric sensors design. Physics and Chemistry of Solid State, 2020, 21, 399-403.	0.3	0
82	Tensometric Characteristics of GaSb Strain Gauges. , 2021, , .		0
83	Development of Inverter Circuits with Dual Control Subchannel Areas of Integral CMOS Sensor Element. Physics and Chemistry of Solid State, 2021, 22, 729-733.	0.3	0
84	Peculiarities of the Magnetoresistance Si<B,Ni> Microcrystals as Sensetive Element of Sensors. , 2022, , .		0